RZ-T Series 32 Bit Arm Based High End MPUs Microprocessors





RENESAS RZ-T Series 32 Bit Arm Based High End MPUs Microprocessors Owner's Manual

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General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

- 1. Precaution against Electrostatic Discharge (ESD) A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device's operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools, including work benches and floors, must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.
- 2. Processing at power-on The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate, and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin,

the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

- 3. Input of signal during power-off state Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from the input of such a signal or I/O pull-up power supply may cause a malfunction and the abnormal current that passes in the device at this time may cause the degradation of internal elements. Follow the guidelines for the input signal during the power-off state as described in your product documentation.
- 4. Handling of unused pins Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal becomes possible.
- 5. Clock signals After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.
- 6. Voltage application waveform at input pin Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (Max.) and VIH (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed and also in the transition period when the input level passes through the area between VIL (Max.) and VIH (Min.).
- 7. 7. Prohibition of access to reserved addresses Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.
- 8. Differences between products Before changing from one product to another, for example, to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

Overview

This guide provides a PCB design method that takes into account fulfilling verification items in "RZ/T2H and RZ/N2H Groups PCB verification guide for LPDDR4" (R01AN7260EJ****). Renesas provides reference design of LPDDR4, which is fully verified according to the verification guide. PCB structures and topologies that are used in this guide refer to reference design. You can copy the PCB layout of the reference design. However, all the verification items listed in the verification guide should be verified through SI and PDN simulations, basically, even if you copied the data. The following documents apply to these LSIs. Make sure to refer to the latest versions of these documents. Last four digits of the document number (described as *****) indicate the version information of each document. The latest versions of the documents listed are obtained from the Renesas Electronics Web site.

List of reference documents

Document Type	Description	Document Title	Document No.
User's manual f or Hardware	Hardware specifications (pin assignments, peripheral function specifications, electrical characteristics, timing charts) and operation description	RZ/T2H and RZ/N2H Groups User's Manual: Hardware	R01UH1039EJ****
Application Not e	PCB verification guide for LPDDR4	RZ/T2H and RZ/N2H Groups PCB Verification Guide for LP DDR4	R01AN7260EJ****

Basic Information

PCB structure

This guide is for an 8-layer board with through-hole vias. Each layer's assignment signal or power (GND) for an 8-layer board is shown in Figure 2.1, the numerical value for each layer indicates its thickness.

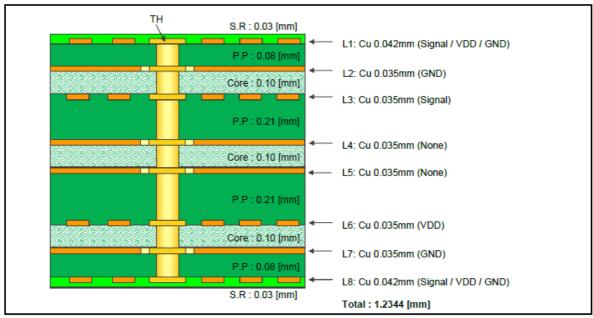


Figure 2.1 PCB structure

• 8-Layer Through-hole

· Base Material: FR-4

• [Dielectric constant : Relative permittivity / Loss tangent]

• Solder Resist (S.R): 3.7/0.017 (for 1GHz)

• Prepreg (P.P) 0.08 mm: 4.2/0.012 (for 1GHz)

• Prepreg (P.P) 0.21 mm: 4.6/0.010 (for 1GHz)

• Core: 4.6/0.010 (for 1GHz)

Design rules

· VIA specifications

VIA diameter: 0.25mm

· Surface land diameter: 0.5mm

• Internal layer land diameter: 0.5mm

• Internal layer clearance diameter: 0.7mm

• VIA center – VIA center : 0.8mm (LSI)

• VIA land - VIA land: 0.3mm (LSI)

VIA center – VIA center : 0.65mm (DRAM)

• VIA land – VIA land: 0.15mm (DRAM)

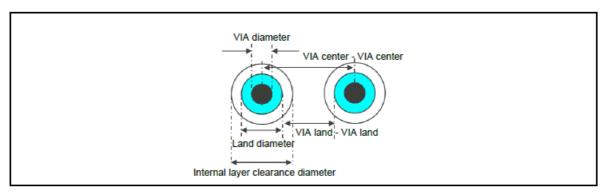


Figure 2.2 VIA specifications

• Minimum trace width: 0.1mm

· Minimum space

• Wiring – Wiring: 0.1mm

• Wiring – VIA: 0.1mm

• Wiring – BGA land: 0.1mm

• VIA - BGA land: 0.1mm

Wiring – BGA resist: 0.05mm

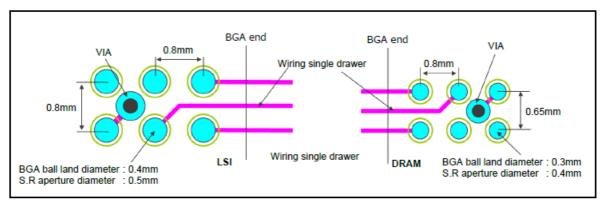


Figure 2.3 BGA land diameter (PAD dimension)

Net swap

Net swap restriction

Some of the external pins are swappable. No register settings are required since the DDR parameter generation tool (gen_tool) provides the swap setting. As for the detail of external pin swizzling, refer to "RZ/T2H and RZ/N2H Groups User's Manual: Hardware, 57.4.1 External Pin Swizzling" (R01UH1039EJ****) and the DDR parameter generation tool.

Example of swizzling for RZ/T2H

Table 3.1 shows an example of swizzling supported by reference design PCB layout data for RZ/T2H.

Table 3.1 Example of swizzling for RZ/T2H (1 of 3)

RZ/T2H		LPDDR4		- Remark
Pin No	Signal name	Pin No	Signal name	Tiemark
K2	DDR_DQA0	F11	DQA11	
K3	DDR_DQA1	F9	DQA12	
K1	DDR_DQA2	E11	DQA10	
K4	DDR_DQA3	E9	DQA13	
J1	DDR_DQA4	C9	DQA14	
H2	DDR_DQA5	B9	DQA15	
H1	DDR_DQA6	C11	DQA9	
J4	DDR_DQA7	B11	DQA8	
F2	DDR_DQA8	B4	DQA7	
E2	DDR_DQA9	C2	DQA1	
G3	DDR_DQA10	C4	DQA6	
F3	DDR_DQA11	E2	DQA2	
E1	DDR_DQA12	F2	DQA3	
E4	DDR_DQA13	B2	DQA0	
F4	DDR_DQA14	F4	DQA4	
G1	DDR_DQA15	E4	DQA5	
J3	DDR_DMIA0	C10	DMIA1	
G4	DDR_DMIA1	C3	DMIA0	
K5	DDR_DQSA_T0	D10	DQSA_T1	
G5	DDR_DQSA_T1	D3	DQSA_T0	
J5	DDR_DQSA_C0	E10	DQSA_C1	
F5	DDR_DQSA_C1	E3	DQSA_C0	

Example of swizzling for RZ/T2H (2 of 3)

RZ/T2H		LPDDR4		- Remark
Pin No	Signal name	Pin No	Signal name	Tiemark
U4	DDR_DQB0	U9	DQB12	
V2	DDR_DQB1	V9	DQB13	
V1	DDR_DQB2	U11	DQB11	
V4	DDR_DQB3	Y9	DQB14	
W2	DDR_DQB4	V11	DQB10	
Y3	DDR_DQB5	AA11	DQB8	
Y1	DDR_DQB6	AA9	DQB15	
W3	DDR_DQB7	Y11	DQB9	
AA1	DDR_DQB8	V4	DQB5	
AB2	DDR_DQB9	Y2	DQB1	
AB4	DDR_DQB10	AA2	DQB0	
AC4	DDR_DQB11	AA4	DQB7	
AC1	DDR_DQB12	U2	DQB3	
AC3	DDR_DQB13	V2	DQB2	
AB1	DDR_DQB14	Y4	DQB6	
AA3	DDR_DQB15	U4	DQB4	
W4	DDR_DMIB0	Y10	DMIB1	
AB3	DDR_DMIB1	Y3	DMIB0	
V5	DDR_DQSB_T0	W10	DQSB_T1	
AA5	DDR_DQSB_T1	W3	DQSB_T0	
W5	DDR_DQSB_C0	V10	DQSB_C1	
AB5	DDR_DQSB_C1	V3	DQSB_C0	

Example of swizzling for RZ/T2H (3 of 3)

RZ/T2H		LPDDR4		Domork
Pin No	Signal name	Pin No	Signal name	Remark
N1	DDR_CKA_T	J8	CKA_T	No remapping
M1	DDR_CKA_C	J9	CKA_C	No remapping

M6	DDR_CKEA0	J4	CKEA0	No remapping
L6	DDR_CKEA1	J5	CKEA1	No remapping
M4	DDR_CSA0	H4	CSA0	No remapping
M5	DDR_CSA1	Н3	CSA1	No remapping
P4	DDR_CAA0	H11	CAA4	
L2	DDR_CAA1	H2	CAA0	
N3	DDR_CAA2	H9	CAA2	
M2	DDR_CAA3	J2	CAA1	
M3	DDR_CAA4	H10	CAA3	
N5	DDR_CAA5	J11	CAA5	
R1	DDR_CKB_T	P8	CKB_T	No remapping
T1	DDR_CKB_C	P9	CKB_C	No remapping
R2	DDR_CKEB0	P4	CKEB0	No remapping
P2	DDR_CKEB1	P5	CKEB1	No remapping
Т6	DDR_CSB0	R4	CSB0	No remapping
U6	DDR_CSB1	R3	CSB1	No remapping
P3	DDR_CAB0	R9	CAB2	
T2	DDR_CAB1	R2	CAB0	
T4	DDR_CAB2	R10	CAB3	
U1	DDR_CAB3	R11	CAB4	
U3	DDR_CAB4	P11	CAB5	
T5	DDR_CAB5	P2	CAB1	
P7	DDR_RESET_N	T11	RESET_N	No remapping
R8	DDR_ZN			No remapping
R7	DDR_DTEST			No remapping

P8	DDR_ATEST		No remapping

Common guidelines

Component placement

Figure 4.1 shows component placement assumptions, U1 indicates LSI and M1 indicates DRAM.

• 2RANK case: Place U1 and M1 on L1.

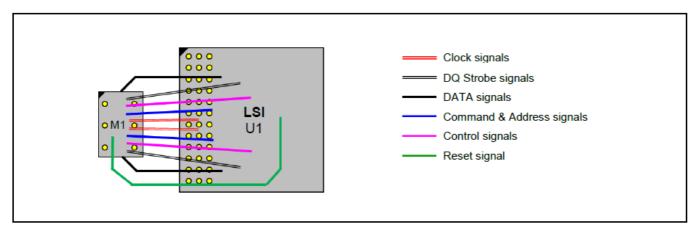


Figure 4.1 Component placement assumptions

IO Power supply layout guideline

The IO power supply (DDR_VDDQ) should be formed on L6 as a plane and should be large enough to cover all signal traces and DRAM. As shown Figure 4.2, place one VIA for every one or two PADs of the IO power supply near the LSI and place a capacitor per number of VIAs. Use GND PADs near DDR_VDDQ place VIAs for GND using the same rule. To shorten the current return path for the IO power supply, consider placing capacitors with the shortest possible trace to the IO power supply and GND. Verify the layout using PDN analysis and check if the results satisfy the specifications described in the verification guide.

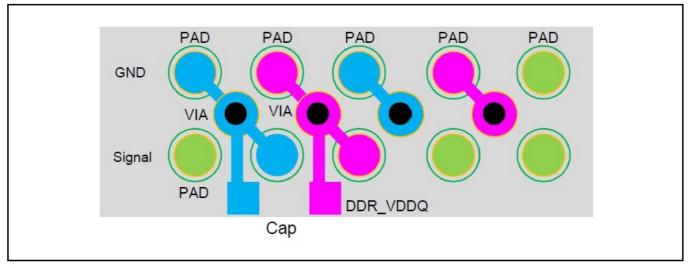


Figure 4.2 IO Power supply layout near the LSI

Topology

As for the detail of skew between wires for each signal, refer to "RZ/T2H and RZ/N2H Groups PCB verification guide for LPDDR4, 4.1.1 Skew restrictions" (R01AN7260EJ****). The PCB configuration of reference design is shown below.

Topology RZ/T2H

System RANK: DualLPDDR4 SDRAM: 64GB

• Target Device: MT53E2G32D4DE-046 AIT:C (Z42N QDP)

• PCB: 8layers / One to One / Top mounting

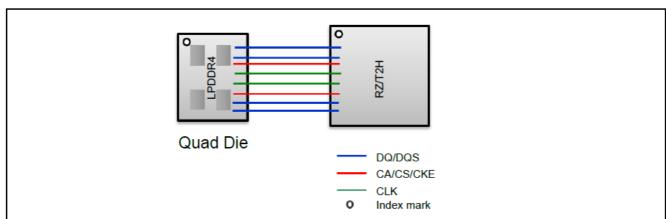


Figure 5.1 PCB configuration

PCB configuration

Table 5.1 shows recommended IO setting. Reference design PCB layout data used 2Rank for DRAM model.

Table 5.1 Recommended IO setting

	LSI		DRAM		Damping r	Number of
Signal	Driver sett ing	ODT	Driver setting	ODT	esistance	Rank
				60Ω		1
CLK	60Ω			60Ω (Rank0 side) OFF (Rank1 side)		2
				60Ω		1
CA	60Ω			60Ω (Rank0 side) OFF (Rank1 side)		2
CS	60Ω			60Ω		1, 2
CKE	FIXED				22Ω	1, 2
RESET	FIXED					1, 2
DQ, DQS				40Ω		1
(Write)	te) 40Ω OFF OFF	OFF	40Ω (access side) OFF (non-access side)		2	
DQ, DQS	OFF 40Ω OE	RONPD = 40Ω LSI ODT = 40Ω VOH = VDDQ / 3	OFF		1	
(Read)			OFF (access side) OFF (non-access side)		2	

CLK topology

Figure 5.2 shows CLK topology. L1 indicates the trace layers, a0 to a0# indicate the trace length. The odd mode impedance (Zodd) is equal to Zdiff/2. The clock traces Zodd should be $40\Omega\pm10\%$. Design the clock following the topology described in this figure.

- 1. CLK pairs should be of equal length. → a0=a0#
- 2. Keep 0.25mm or more between other signal traces.
- 3. Verify the layout using SI simulation and check its result to satisfy the timing and waveform restrictions in the verification guide. (Mandatory).

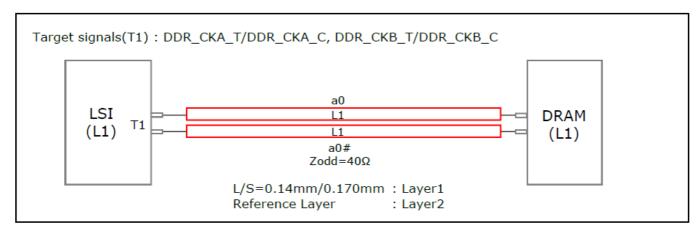


Figure 5.2 CLK topology

CA topology

Figure 5.3 shows CA topology. L1, L3 and L8 indicate the trace layers, a0 to c2 indicate the trace length. " are VIAs. Address and command signals are single-ended, and their impedance (Z0) should be $50\Omega\pm10\%$. Design address and command signals following the topology described in this figure.

1. Verify the layout using SI simulation and check its result to satisfy the timing and waveform restrictions in the verification guide. (Mandatory)

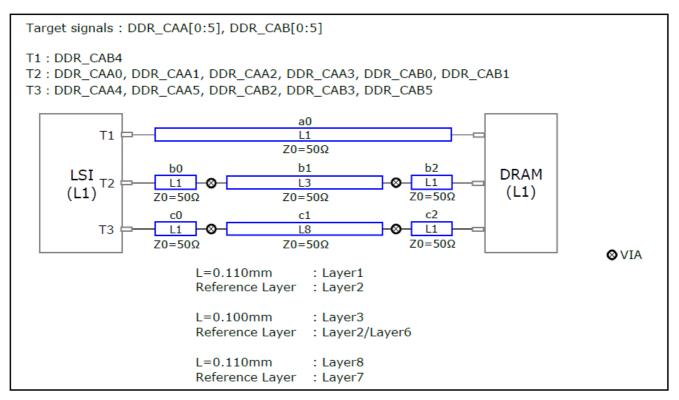


Figure 5.3 CA topology

CTRL topology

Figure 5.4 shows CTRL topology. L1, L3 and L8 indicate the trace layers, a0 to c3 indicate the trace length. " \checkmark are VIAs. Control signals are single-ended, and their impedance (Z0) should be $50\Omega\pm10\%$. Design control signals following the topology described in this figure.

1. Verify the layout using SI simulation and check its result to satisfy the timing and waveform restrictions in the verification guide. (Mandatory)

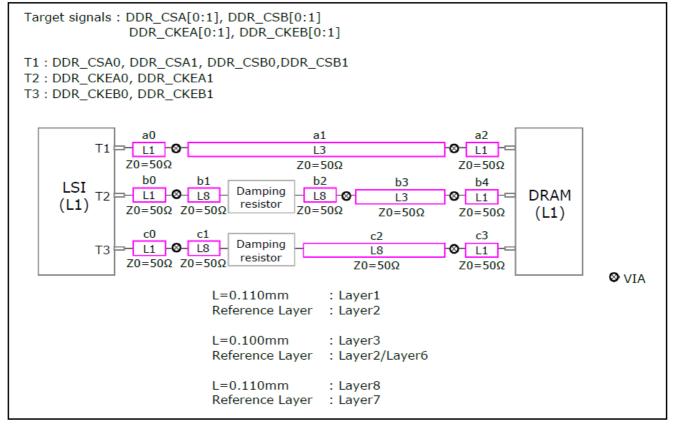


Figure 5.4 CTRL topology

RESET topology

Figure 5.5 shows RESET topology. L1 and L3 indicate trace layers, a0 to a2 indicate the trace length. " are VIAs. The reset signal is single-ended, and his impedances (Z0) should be $50\Omega \pm 10\%$. Design the wiring so that the wiring topology is as shown in this figure.

1. Verify the layout using SI simulation and check its result to satisfy the timing and waveform restrictions in the verification guide. (Mandatory)

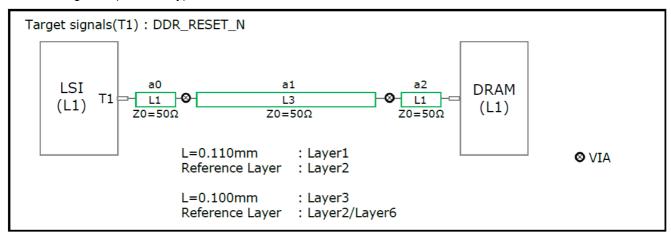


Figure 5.5 RESET topology

DQS/DQ topology

Figure 5.6 and Figure 5.7 show DQS/DQ topology. L1, L3 and L8 in the figure below indicate the trace layers, a0 to b2 indicate the trace length. "" are VIAs. Zodd for DQS and DQS# traces should be $40\Omega\pm10\%$. Z0 for DQ and DM should be $45\Omega\pm10\%$. Design the DQS following the topology described in this figure.

- 1. DQS pairs should be of equal length. → a0=a0#
- 2. Keep 0.25mm or more between other signal traces.
- 3. Verify the layout using SI simulation and check its result to satisfy the timing and waveform restrictions in the verification guide. (Mandatory)

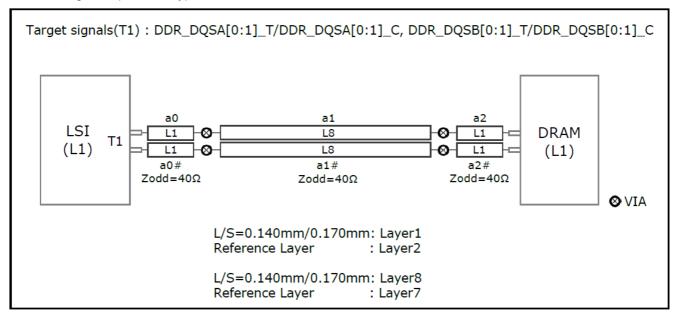


Figure 5.6 DQS topology

Target signals: DDR_DMIA[0:1], DDR_DQA[0:15], DDR_DMIB[0:1], DDR_DQB_[0:15]

Target signals: DDR_DMIA[0:1], DDR_DQA[0:15], DDR_DMIB[0:1], DDR_DQB_[0:15] T1: DDR_DQA1, DDR_DQA5, DDR_DQA6, DDR_DQA7, DDR_DQA9, DDR_DQA10, DDR_DQA11 DDR_DQA15, DDR_DQB1, DDR_DQB5, DDR_DQB6, DDR_DQB9, DDR_DQB10, DDR_DQB11 DDR_DQB15 T2: DDR_DQA0, DDR_DQA2, DDR_DQA3, DDR_DQA4, DDR_DMIA0, DDR_DQA8, DDR_DQA12 DDR DQA13, DDR DQA14, DDR DQB0, DDR DQB2, DDR DQB3, DDR DQB4, DDR DQB7 DDR_DMIB0, DDR_DQB8, DDR_DQB12, DDR_DQB13, DDR_DQB14, DDR_DMIB1 T3: DDR_DMIA1 a0 T1 Z0=45Ω b1 b₀ b2 LSI DRAM T2 L3 (L1)(L1) Z0=45Ω $Z0 = 45\Omega$ Z0=45Ω c0 c1 L8 T3 L1 Z0=45Ω ⊗ VIA Z0=45Ω 70=450 L=0.135mm : Layer1 Reference Layer : Layer2 L=0.130mm : Layer3 Reference Layer : Layer2/Layer6 L=0.135mm : Layer8 Reference Layer : Layer7

Figure 5.7 DQ topology

Handling of Other Pins

Handling of Other Pins is as follows.

- DDR_ZN: 120 (±1%) Ω external resistor must be connected between DDR_ZN and VSS (GND).
- DDR DTEST, DDR ATEST: Keep these pins open.

		Description			
Rev	Date	Page	Summary		
0.70	Mar 26, 20 24	3/4	First Preliminary Edition issued		
	Sep 30, 20	5	1 Overview: Description about reference design, added.		
1.00	1.00 36p 30, 20	8	3.1 Net swap restriction: Description about DDR parameter generation tool, added.		

RZ/T2H and RZ/N2H Groups PCB Design Guide for LPDDR4

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RENESAS RZ-T Series 32 Bit Arm Based High End MPUs Microprocessors [pdf] Owner's M anual

RZ-T Series, RZ-T Series 32 Bit Arm Based High End MPUs Microprocessors, 32 Bit Arm Based High End MPUs Microprocessors, High End MPUs Microprocessors, Microprocessors

References

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